

# PSMN7R0-30YL

# N-channel 30 V 7 mΩ logic level MOSFET in LFPAK Rev. 04 — 9 March 2011 Product

Product data sheet

#### **Product profile** 1.

#### 1.1 General description

Logic level N-channel enhancement mode Field-Effect Transistor (FET) in a plastic package using TrenchMOS technology. This product is designed and qualified for use in industrial and communications applications.

#### 1.2 Features and benefits

- High efficiency due to low switching and conduction losses
- Suitable for logic level gate drive sources

### 1.3 Applications

- Class-D amplifiers
- DC-to-DC converter

- Motor control
- Server power supplies

#### 1.4 Quick reference data

Table 1. Quick reference data

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
$V_{DS}$	drain-source voltage	$T_j \ge 25 \text{ °C}; T_j \le 175 \text{ °C}$	-	-	30	V
I <sub>D</sub>	drain current	$T_{mb} = 25 \text{ °C}; V_{GS} = 10 \text{ V};$ see Figure 1	-	-	76	Α
P <sub>tot</sub>	total power dissipation	T <sub>mb</sub> = 25 °C; see <u>Figure 2</u>	-	-	51	W
Tj	junction temperature		-55	-	175	°C
Static chara	acteristics					
R <sub>DSon</sub>	drain-source on-state resistance	$V_{GS} = 10 \text{ V}; I_D = 15 \text{ A};$ $T_j = 25 \text{ °C}$	-	4.92	7	mΩ
Dynamic ch	naracteristics					
$Q_{GD}$	gate-drain charge	$V_{GS} = 4.5 \text{ V}; I_D = 10 \text{ A};$	-	2.9	-	nC
Q <sub>G(tot)</sub>	total gate charge	V <sub>DS</sub> = 12 V; see <u>Figure 14</u> ; see <u>Figure 15</u>	-	10	-	nC
Avalanche ruggedness						
E <sub>DS(AL)S</sub>	non-repetitive drain-source avalanche energy	$V_{GS} = 10 \text{ V; } T_{j(init)} = 25 \text{ °C;}$ $I_D = 65 \text{ A; } V_{sup} \le 30 \text{ V;}$ $R_{GS} = 50 \Omega; \text{ unclamped}$	-	-	21	mJ



# 2. Pinning information

Table 2. Pinning information

Pin	Symbol	Description	Simplified outline	Graphic symbol
1	S	source		
2	S	source	mb	D
3	S	source		
4	G	gate	Q	
mb	D	mounting base; connected to drain	1 2 3 4	mbb076 S
			SOT669 (LFPAK)	

# 3. Ordering information

Table 3. Ordering information

Type number	Package		
	Name	Description	Version
PSMN7R0-30YL	LFPAK	plastic single-ended surface-mounted package (LFPAK); 4 leads	SOT669

# 4. Limiting values

Table 4. Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134).

Symbol	Parameter	Conditions	Min	Max	Unit
$V_{DS}$	drain-source voltage	T <sub>j</sub> ≥ 25 °C; T <sub>j</sub> ≤ 175 °C	-	30	V
$V_{DSM}$	peak drain-source voltage	$t_p \le 25 \text{ ns; } f \le 500 \text{ kHz; } E_{DS(AL)} \le 90 \text{ nJ;}$ pulsed	-	35	V
$V_{DGR}$	drain-gate voltage	$T_j \ge 25$ °C; $T_j \le 175$ °C; $R_{GS} = 20$ kΩ	-	30	V
$V_{GS}$	gate-source voltage		-20	20	V
$I_D$	drain current	$V_{GS} = 10 \text{ V}; T_{mb} = 100 \text{ °C}; \text{ see } \frac{\text{Figure 1}}{\text{Model}}$	-	53	Α
		$V_{GS} = 10 \text{ V}; T_{mb} = 25 \text{ °C}; \text{ see } \underline{\text{Figure 1}}$	-	76	Α
I <sub>DM</sub>	peak drain current	pulsed; $t_p \le 10 \mu s$ ; $T_{mb} = 25 \text{ °C}$ ; see Figure 3	-	260	Α
P <sub>tot</sub>	total power dissipation	T <sub>mb</sub> = 25 °C; see <u>Figure 2</u>	-	51	W
T <sub>stg</sub>	storage temperature		-55	175	°C
Tj	junction temperature		-55	175	°C
Source-drain	diode				
Is	source current	T <sub>mb</sub> = 25 °C	-	65	Α
I <sub>SM</sub>	peak source current	pulsed; $t_p \le 10 \ \mu s$ ; $T_{mb} = 25 \ ^{\circ}C$	-	260	Α
Avalanche ruç	ggedness				
E <sub>DS(AL)S</sub>	non-repetitive drain-source avalanche energy	$V_{GS}$ = 10 V; $T_{j(init)}$ = 25 °C; $I_{D}$ = 65 A; $V_{sup}$ ≤ 30 V; $R_{GS}$ = 50 Ω; unclamped	-	21	mJ

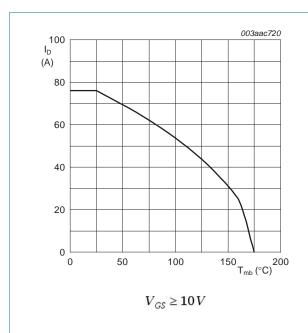


Fig 1. Continuous drain current as a function of mounting base temperature

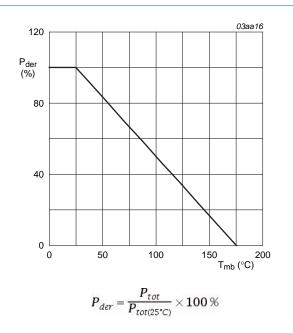
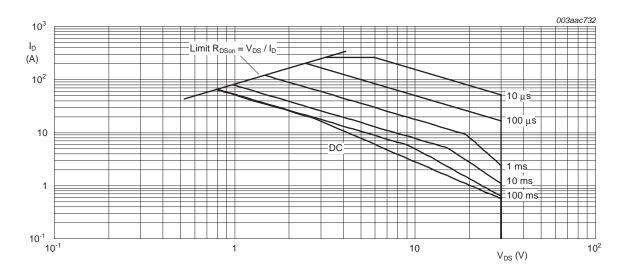


Fig 2. Normalized total power dissipation as a function of mounting base temperature



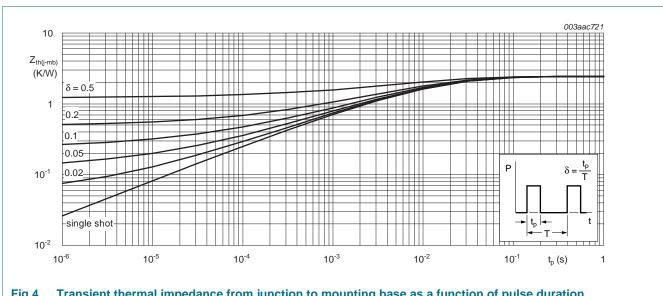
 $T_{mb} = 25 \,^{\circ}C; I_{DM}$ is single pulse

Fig 3. Safe operating area; continuous and peak drain currents as a function of drain-source voltage

## **Thermal characteristics**

Table 5. **Thermal characteristics** 

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
$R_{th(j-mb)}$	thermal resistance from junction to mounting base	see Figure 4	-	1.4	2.45	K/W



Transient thermal impedance from junction to mounting base as a function of pulse duration

## 6. Characteristics

Table 6. Characteristics

Tested to JEDEC standards where applicable.

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
Static chara	cteristics					
V <sub>(BR)DSS</sub>	drain-source	$I_D = 250 \mu A; V_{GS} = 0 V; T_j = 25 °C$	30	-	-	V
	breakdown voltage	$I_D = 250 \mu A; V_{GS} = 0 V; T_j = -55 °C$	27	-	-	V
$V_{GS(th)}$	gate-source threshold voltage	$I_D = 1$ mA; $V_{DS} = V_{GS}$ ; $T_j = 25$ °C; see <u>Figure 11</u> ; see <u>Figure 12</u>	1.3	1.7	2.15	V
		$I_D$ = 1 mA; $V_{DS}$ = $V_{GS}$ ; $T_j$ = 150 °C; see <u>Figure 12</u>	0.65	-	-	V
		$I_D = 1$ mA; $V_{DS} = V_{GS}$ ; $T_j = -55$ °C; see Figure 12	-	-	2.45	V
I <sub>DSS</sub>	drain leakage current	$V_{DS} = 30 \text{ V}; V_{GS} = 0 \text{ V}; T_j = 25 \text{ °C}$	-	-	1	μΑ
		$V_{DS} = 30 \text{ V}; V_{GS} = 0 \text{ V}; T_j = 150 \text{ °C}$	-	-	100	μΑ
$I_{GSS}$	gate leakage current	$V_{GS} = 16 \text{ V}; V_{DS} = 0 \text{ V}; T_j = 25 \text{ °C}$	-	-	100	nΑ
		$V_{GS} = -16 \text{ V}; V_{DS} = 0 \text{ V}; T_j = 25 \text{ °C}$	-	-	100	nΑ
R <sub>DSon</sub>	drain-source on-state	$V_{GS} = 4.5 \text{ V}; I_D = 15 \text{ A}; T_j = 25 \text{ °C}$	-	6.97	9.1	mΩ
	resistance	$V_{GS} = 10 \text{ V}; I_D = 15 \text{ A}; T_j = 150 \text{ °C};$ see Figure 13	-	-	12.2	mΩ
		$V_{GS} = 10 \text{ V}; I_D = 15 \text{ A}; T_j = 25 \text{ °C}$	-	4.92	7	mΩ
$R_{G}$	gate resistance	f = 1 MHz	-	0.6	1.5	Ω
Dynamic ch	aracteristics					
Q <sub>G(tot)</sub>	total gate charge	$I_D = 10 \text{ A}$ ; $V_{DS} = 12 \text{ V}$ ; $V_{GS} = 4.5 \text{ V}$ ; see Figure 14; see Figure 15	-	10	-	nC
		$I_D = 0 \text{ A}; V_{DS} = 0 \text{ V}; V_{GS} = 10 \text{ V}$	-	20	-	nC
		$I_D = 10 \text{ A}$ ; $V_{DS} = 12 \text{ V}$ ; $V_{GS} = 10 \text{ V}$ ; see Figure 14; see Figure 15	-	22	-	nC
Q <sub>GS</sub>	gate-source charge	$I_D = 10 \text{ A}$ ; $V_{DS} = 12 \text{ V}$ ; $V_{GS} = 4.5 \text{ V}$ ;	-	3.7	-	nC
Q <sub>GS(th)</sub>	pre-threshold gate-source charge	see <u>Figure 14;</u> see <u>Figure 15</u>	-	2.1	-	nC
Q <sub>GS(th-pl)</sub>	post-threshold gate-source charge		-	1.6	-	nC
$Q_{GD}$	gate-drain charge		-	2.9	-	nC
$V_{GS(pl)}$	gate-source plateau voltage	V <sub>DS</sub> = 12 V; see <u>Figure 14</u> ; see <u>Figure 15</u>	-	2.6	-	V
C <sub>iss</sub>	input capacitance	$V_{DS} = 12 \text{ V}; V_{GS} = 0 \text{ V}; f = 1 \text{ MHz};$	-	1270	-	pF
C <sub>oss</sub>	output capacitance	T <sub>j</sub> = 25 °C; see <u>Figure 16</u>	-	255	-	pF
C <sub>rss</sub>	reverse transfer capacitance		-	145	-	pF
t <sub>d(on)</sub>	turn-on delay time	$V_{DS} = 12 \text{ V}; R_L = 0.5 \Omega; V_{GS} = 4.5 \text{ V};$	-	24	-	ns
t <sub>r</sub>	rise time	$R_{G(ext)} = 4.7 \Omega$	-	39	-	ns
t <sub>d(off)</sub>	turn-off delay time		-	30	-	ns
t <sub>f</sub>	fall time		-	11	-	ns

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 Table 6.
 Characteristics ...continued

Tested to JEDEC standards where applicable.

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
Source-drain	diode					
$V_{SD}$	source-drain voltage	$I_S = 25 \text{ A}$ ; $V_{GS} = 0 \text{ V}$ ; $T_j = 25 \text{ °C}$ ; see <u>Figure 17</u>	-	0.88	1.2	V
t <sub>rr</sub>	reverse recovery time	$I_S = 20 \text{ A}$ ; $dI_S/dt = -100 \text{ A/}\mu\text{s}$ ; $V_{GS} = 0 \text{ V}$ ;	-	30	-	ns
Q <sub>r</sub>	recovered charge	V <sub>DS</sub> = 20 V	-	22	-	nC

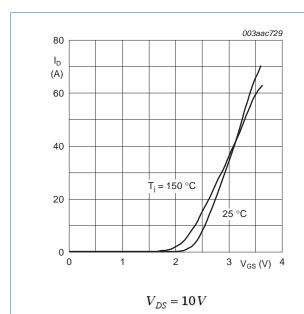


Fig 5. Transfer characteristics: drain current as a function of gate-source voltage; typical values

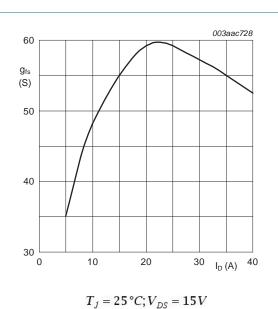


Fig 6. Forward transconductance as a function of drain current; typical values

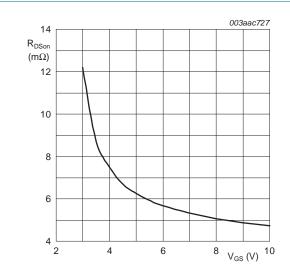
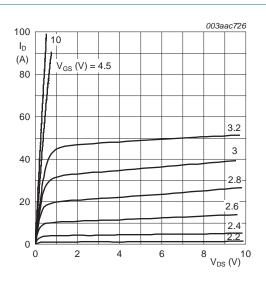


Fig 7. Drain-source on-state resistance as a function of gate-source voltage; typical values

 $T_j = 25 \,{}^{\circ}C; I_D = 15A$ 



 $T_j = 25 \,^{\circ}C; t_p = 300 \mu s$ 

Fig 8. Output characteristics: drain current as a function of drain-source voltage; typical values

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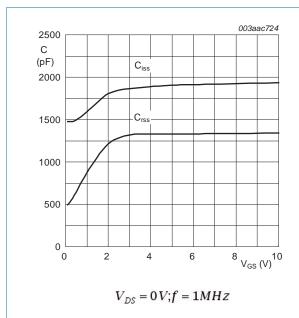


Fig 9. Input and reverse transfer capacitances as a function of gate-source voltage; typical values

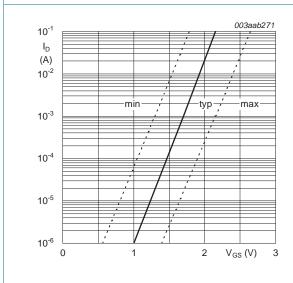
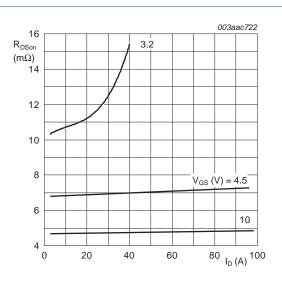


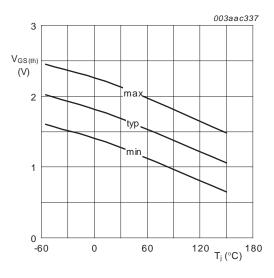
Fig 11. Sub-threshold drain current as a function of gate-source voltage

 $T_j = 25 \,^{\circ}C; V_{DS} = 5V$ 



$$T_j = 25 \,^{\circ}C; t_p = 300 \mu s$$

Fig 10. Drain-source on-state resistance as a function of drain current; typical values



 $I_D = 1mA; V_{DS} = V_{GS}$ 

Fig 12. Gate-source threshold voltage as a function of junction temperature

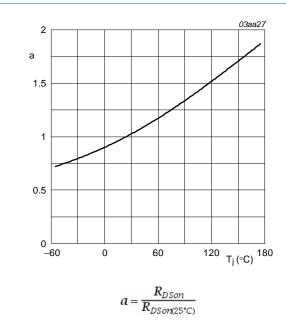


Fig 13. Normalized drain-source on-state resistance factor as a function of junction temperature

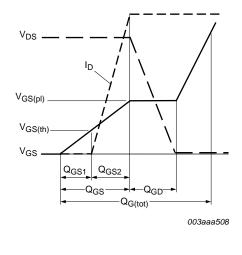


Fig 14. Gate charge waveform definitions

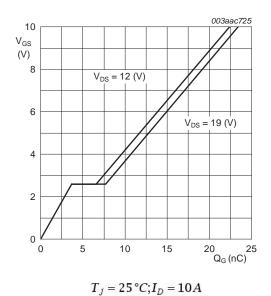
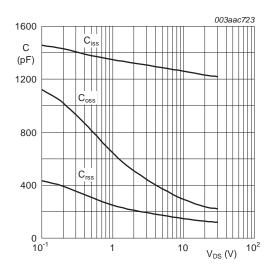


Fig 15. Gate-source voltage as a function of gate charge; typical values



 $V_{GS} = 0V; f = 1MHz$ 

Fig 16. Input, output and reverse transfer capacitances as a function of drain-source voltage; typical values

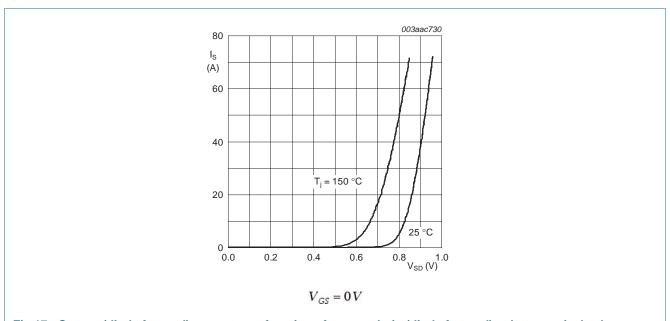


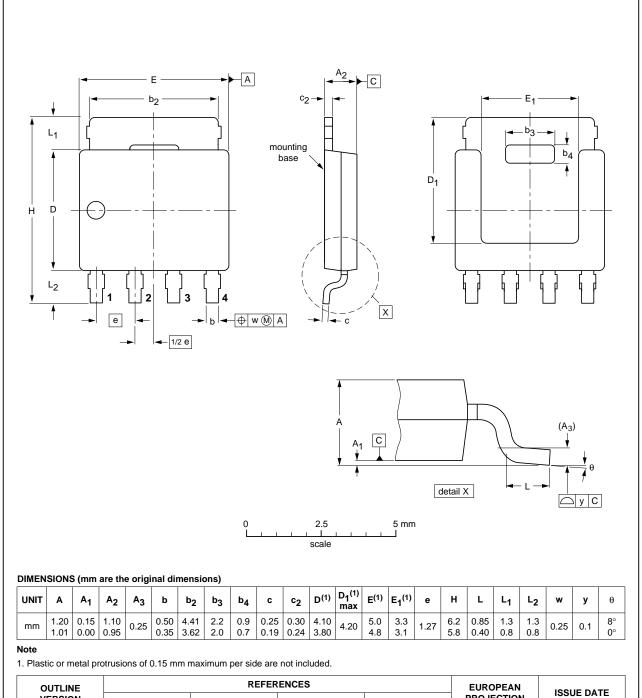
Fig 17. Source (diode forward) current as a function of source-drain (diode forward) voltage; typical values

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## 7. Package outline

## Plastic single-ended surface-mounted package (LFPAK); 4 leads

**SOT669** 



OUTLINE		REFER	ENCES	EUROPEAN ISSUE DA		
VERSION	IEC	JEDEC	JEITA	PROJECTION	ISSUE DATE	
SOT669		MO-235			<del>04-10-13</del> 06-03-16	

Fig 18. Package outline SOT669 (LFPAK)

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# 8. Revision history

#### Table 7. Revision history

Document ID	Release date	Data sheet status	Change notice	Supersedes
PSMN7R0-30YL v.4	20110309	Product data sheet	-	PSMN7R0-30YL v.3
Modifications:	<ul> <li>Various changes to</li> </ul>	content.		
PSMN7R0-30YL v.3	20100104	Product data sheet	-	PSMN7R0-30YL v.2
PSMN7R0-30YL v.2	20090105	Product data sheet	-	PSMN7R0-30YL v.1
PSMN7R0-30YL v.1	20081015	Preliminary data sheet	-	-

## 9. Legal information

#### 9.1 Data sheet status

Document status [1] [2]	Product status [3]	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
Preliminary [short] data sheet	Qualification	This document contains data from the preliminary specification.
Product [short] data sheet	Production	This document contains the product specification.

- [1] Please consult the most recently issued document before initiating or completing a design.
- [2] The term 'short data sheet' is explained in section "Definitions".
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## **Nexperia**

N-channel 30 V 7 mΩ logic level MOSFET in LFPAK

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